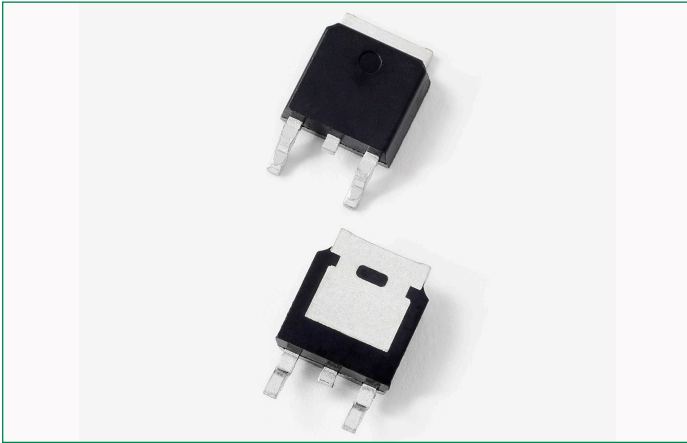


# SRU6008xSx

## 8 A Sensitive SCR (reverse undefined)

RoHS



### Description:

The SRU6008xSx SCR series is specifically designed for high voltage capacitor discharge applications.

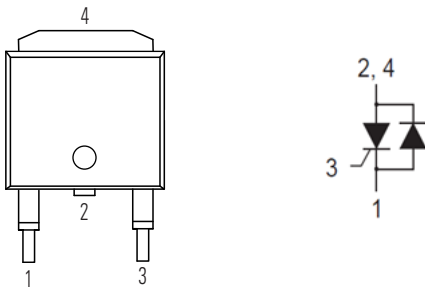
### Features and Benefits:

- High forward blocking voltage of 600 V
- High pulse current handling capacity
- High di/dt of 100 A/μs
- Reverse direction not designed to function

### Applications:

Typical applications are high voltage pulse generation by capacitor discharge for electric fences, CEWs (contact electric weapon) and high-power strobe lights.

### Pinout Diagram



**1:** Cathode; **2:** Anode; **3:** Gate; **4:** Anode

### Product Summary

Characteristic	Value	Unit
$I_{T(RMS)}$	8	A
$V_{DRM}$	600	V
$V_{RRM}$	N/A	V
$I_{GT}$	0.2	mA

## Absolute Maximum Ratings – Sensitive SCRs

Symbol	Characteristics	Conditions	Value	Units
$V_{DSM}$	Non-repetitive Peak Off-state Voltage	$T_J = 25^\circ\text{C}$	800	V
$I_{T(RMS)}$	RMS On-state Current	$T_C = 130^\circ\text{C}$	8	A
$I_{T(AV)}$	Average On-state Current		5.1	
$I_{TSM}$	Peak Non-repetitive Surge Current	Single Half Cycle, $f = 50\text{ Hz}$ , $T_J(\text{initial}) = 25^\circ\text{C}$	83	A
		Single Half Cycle, $f = 60\text{ Hz}$ , $T_J(\text{initial}) = 25^\circ\text{C}$	100	
$I^2t$	$I^2t$ Value for Fusing	$t_p = 8.3\text{ ms}$	41	$\text{A}^2\text{s}$
$di/dt$	Critical Rate-of-Rise of On-state Current	$T_J = 150^\circ\text{C}$ $f = 60\text{ Hz}$	100	$\text{A}/\mu\text{s}$
$I_{GM}$	Peak Gate Current	$P_W = 20\ \mu\text{s}$ $T_J = 150^\circ\text{C}$	0.5	A
$P_{G(AV)}$	Average Gate Power Dissipation	$T_J = 150^\circ\text{C}$	0.1	W
$T_{stg}$	Storage Temperature Range	–	–40 to 150	$^\circ\text{C}$
$T_J$	Operating Junction Temperature Range	–	–40 to 150	$^\circ\text{C}$

## Electrical Characteristics ( $T_J = 25^\circ\text{C}$ unless otherwise specified)

Symbol	Characteristic	Conditions	Value			Unit
			Min.	Typ.	Max.	
$I_{GT}$	Gate Trigger Current	$V_D = 12\text{ V}$ $R_L = 60\ \Omega$	20	–	–	$\mu\text{A}$
			–	–	200	
$V_{GT}$	Gate Trigger Voltage		–	–	0.8	V
$dv/dt$	Critical Rate of Rise of Off-stage Voltage	$V_D = V_{DRM}$ ; $RGK = 220\ \Omega$ ; $T_J = 125^\circ\text{C}$	15	–	–	$\text{V}/\mu\text{s}$
$V_{GD}$	Gate Non-trigger Voltage	$V_D = V_{DRM}$ $R_L = 3.3\text{ k}\Omega$ $T_J = 150^\circ\text{C}$	0.1	–	–	V
$I_H$	Holding Current	$I_T = 200\text{ mA}$ (initial)	–	–	6	mA
$t_q$	Turn-off Time	$I_T = 0.5\text{ A}$ ; $t_p = 50\ \mu\text{s}$ ; $dv/dt = 5\text{ V}/\mu\text{s}$ ; $di/dt = -30\text{ A}/\mu$	–	55	–	$\mu\text{s}$
$t_{gt}$	Turn-on Time	$I_G = 2 \times I_{GT}$ $P_W = 15\ \mu\text{s}$ $I_T = 16\text{ A}$	–	1	–	$\mu\text{s}$
$V_{GRM}$	Peak Reverse Gate Voltage	$I_{GR} = 10\ \mu\text{A}$	6	–	–	V

## Static Characteristics

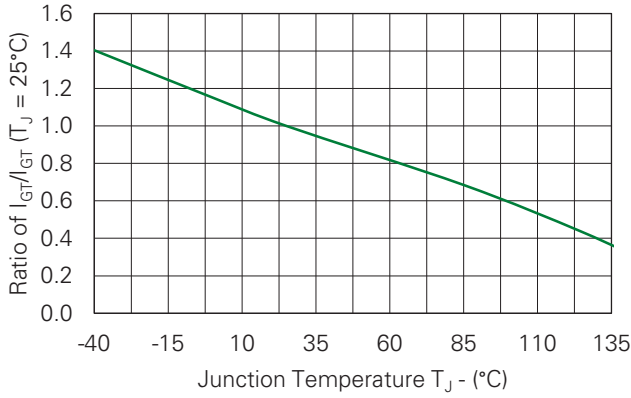
Symbol	Characteristic	Conditions	Value			Unit	
			Min.	Typ.	Max.		
$V_{TM}$	Peak On-state Voltage Drop	$I_T = 16\text{ A}$ ; $t_p = 380\ \mu\text{s}$	–	–	1.6	V	
$I_{DRM}$	Repetitive Peak Off-state Current	$V_D = V_{DRM} = 600\text{ V}$	$T_J = 25^\circ\text{C}$	–	–	5	$\mu\text{A}$
			$T_J = 150^\circ\text{C}$ ; $RGK = 220\ \Omega$	–	–	2	mA

## Thermal Resistances

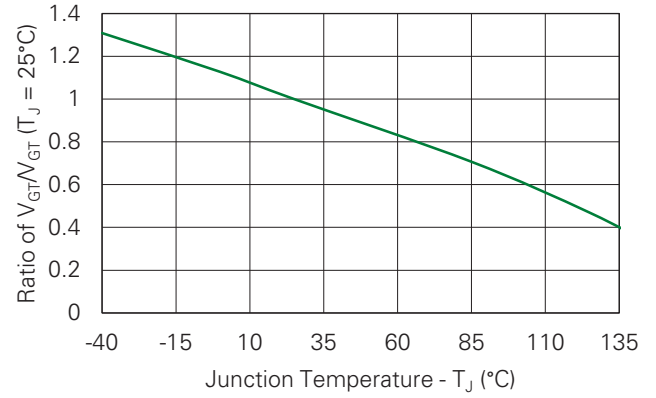
Symbol	Characteristic	Conditions	Value	Unit
$R_{\theta(JC)}$	Thermal Resistance, Junction to case (AC)	–	1.2	$^\circ\text{C}/\text{W}$

**Characteristic Curves**

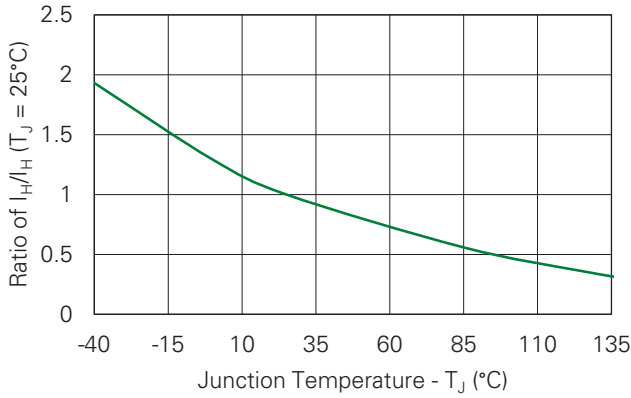
**Fig. 1. Normalized DC Gate Trigger Current vs. Junction Temperature**



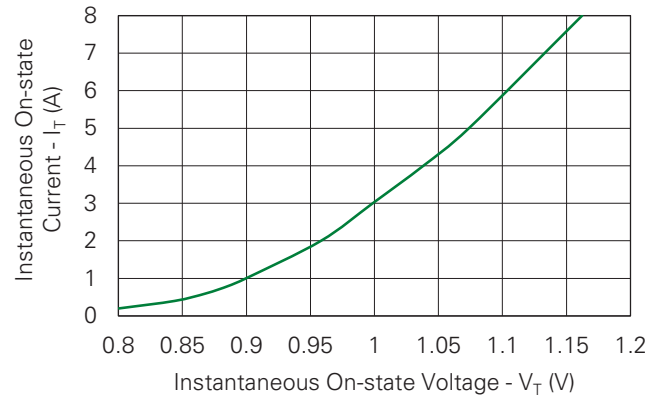
**Fig. 2. Normalized DC Gate Trigger Voltage vs. Junction Temperature**



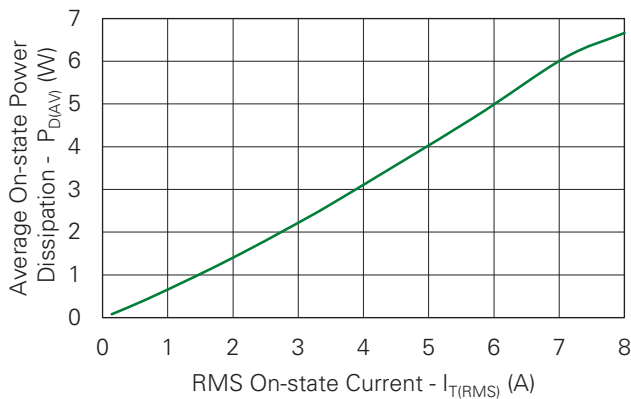
**Fig. 3. Normalized DC Holding Current vs. Junction Temperature**



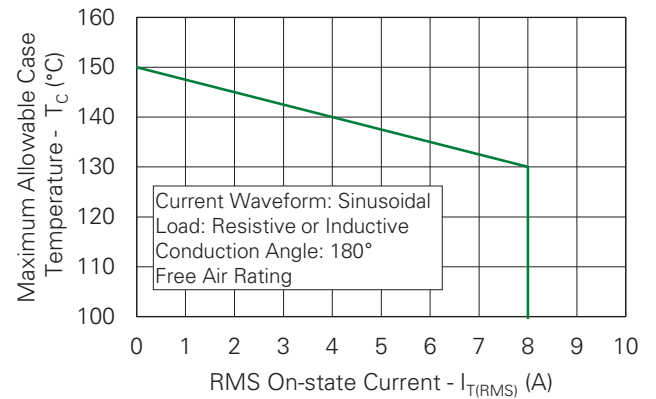
**Fig. 4. Typical On-state Current vs. On-state Voltage**



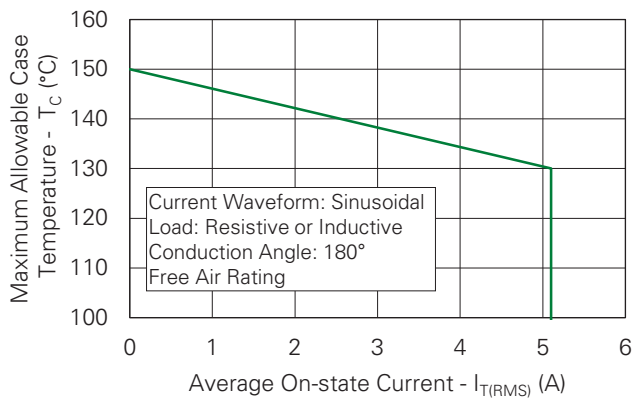
**Fig. 5. Typical Power Dissipation vs. RMS On-state Current**



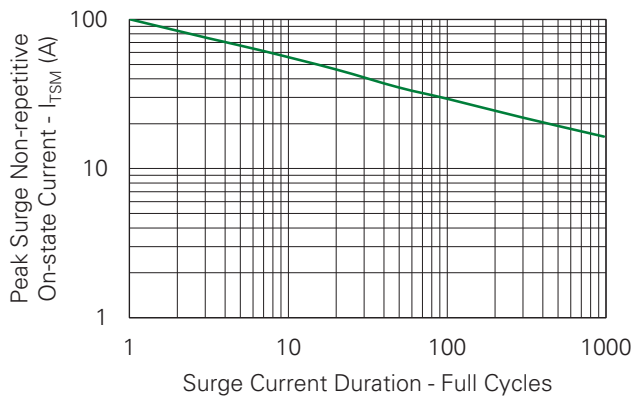
**Fig. 6. Maximum Allowable Case Temperature vs. RMS On-state Current**



**Fig. 7. Maximum Allowable Case Temperature vs. Average On-state Current**



**Fig. 8. Surge Peak On-state Current vs. Number of Cycles**



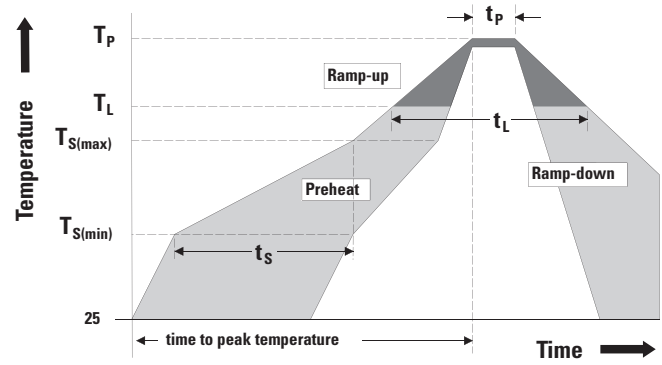
SUPPLY FREQUENCY: 60 Hz Sinusoidal  
LOAD: Resistive  
RMS On-State Current: [ $I_{T(RMS)}$ ]: Maximum Rated Value at Specified Case Temperature

Notes:

1. Gate control may be lost during and immediately following surge current interval.
2. Overload may not be repeated until junction temperature has returned to steady-state rated value.

## Soldering Parameters

Characteristic		Value
Reflow Condition		Pb – Free assembly
Pre-heat	Temperature Min ( $T_{s(min)}$ )	150°C
	Temperature Max ( $T_{s(max)}$ )	200°C
	Time (min to max) ( $t_s$ )	60 – 120 secs
Average ramp up rate (Liquidus Temp)( $T_L$ ) to peak		3°C/second max
$T_{s(max)}$ to $T_L$ - Ramp-up Rate		3°C/second max
Reflow	Temperature ( $T_L$ ) (Liquidus)	217°C
	Time ( $t_L$ )	60 – 150 seconds
Peak Temperature ( $T_p$ )		260 <sup>+0/-5</sup> °C
Time within 5°C of actual peak Temperature ( $t_p$ )		30 seconds max
Ramp-down Rate		6°C/second max
Time 25°C to peak Temperature ( $T_p$ )		8 minutes max
Do Not Exceed		260°C



## Physical Specifications

Characteristic	Value
Terminal Finish	100% Matte Tin-plated
Body Material	UL Recognized compound meeting flammability rating V-0
Lead Material	Copper Alloy

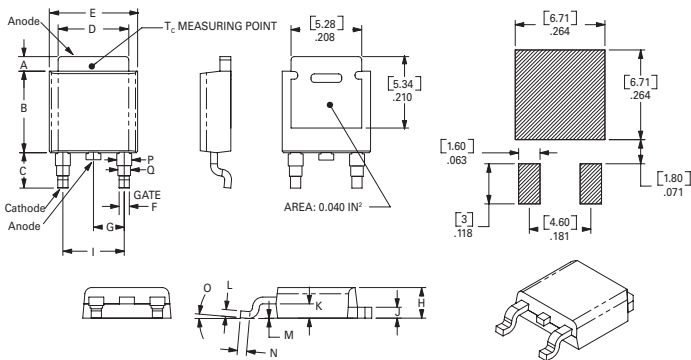
## Design Considerations

Careful selection of the correct component for the application's operating parameters and environment will go a long way toward extending the operating life of the Thyristor. Good design practice should limit the maximum continuous current through the main terminals to 75% of the component rating. Other ways to ensure long life for a power discrete semiconductor are proper heat sinking and selection of voltage ratings for worst case conditions. Overheating, overvoltage (including  $dv/dt$ ), and surge currents are the main killers of semiconductors. Correct mounting, soldering, and forming of the leads also help protect against component damage.

## Environmental Specifications

Test	Specifications and Conditions
AC Blocking	MIL-STD-750, M-1040, Cond A Applied Peak AC voltage for 1008 hours
Temperature/Humidity	EIA / JEDEC, JESD22-A101, 1008 hours; 160V - DC: 85°C; 85% relative humidity
Temperature Cycling	MIL-STD-750, M-1051, 1000 cycles; -55°C to +150°C; 15-min dwell-time
Resistance to Solder Heat	MIL-STD-750 Method 2031
Solderability	ANSI/J-STD-002, category 3, Test A
Moisture Sensitivity Level	Level 1

Part Outline Drawing (TO-252AA) (D Package) – DPAK Surface Mount

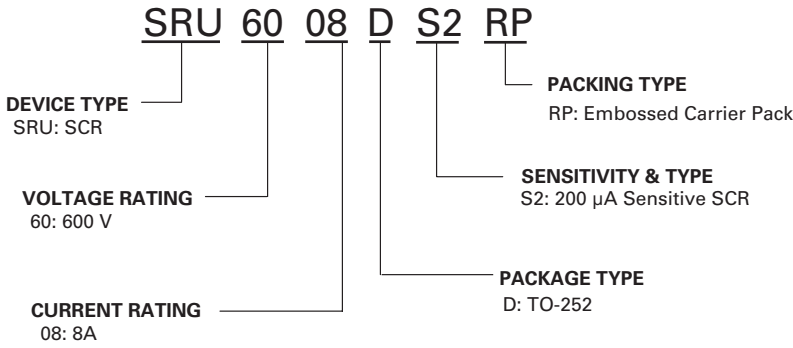


Symbol	Inches			Millimeters		
	Min.	Typical	Max.	Min.	Typical	Max
A	0.037	0.040	0.043	0.94	1.01	1.09
B	0.235	0.243	0.245	5.97	6.16	6.22
C	0.106	0.108	0.113	2.69	2.74	2.87
D	0.205	0.208	0.213	5.21	5.29	5.41
E	0.255	0.262	0.265	6.48	6.65	6.73
F	0.027	0.031	0.033	0.69	0.80	0.84
G	0.087	0.090	0.093	2.21	2.28	2.36
H	0.085	0.092	0.095	2.16	2.33	2.41
I	0.176	0.179	0.184	4.47	4.55	4.67
J	0.018	0.020	0.023	0.46	0.51	0.58
K	0.035	0.037	0.039	0.90	0.95	1.00
L	0.018	0.020	0.023	0.46	0.51	0.58
M	0.000	0.000	0.004	0.00	0.00	0.10
N	0.021	0.026	0.027	0.53	0.67	0.69
O	0°	0°	5°	0°	0°	5°
P	0.042	0.047	0.052	1.06	1.20	1.32
Q	0.034	0.039	0.044	0.86	1.00	1.11

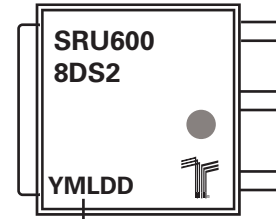
Packing Options

Part Number	Marking	Package	Type	Weight	Packing Mode	Base Quantity
SRU6008DS2RP	SRU6008DS2	TO-252	Sensitive SCR	0.3 g	Embossed Carrier	2500

## Part Numbering and Marking



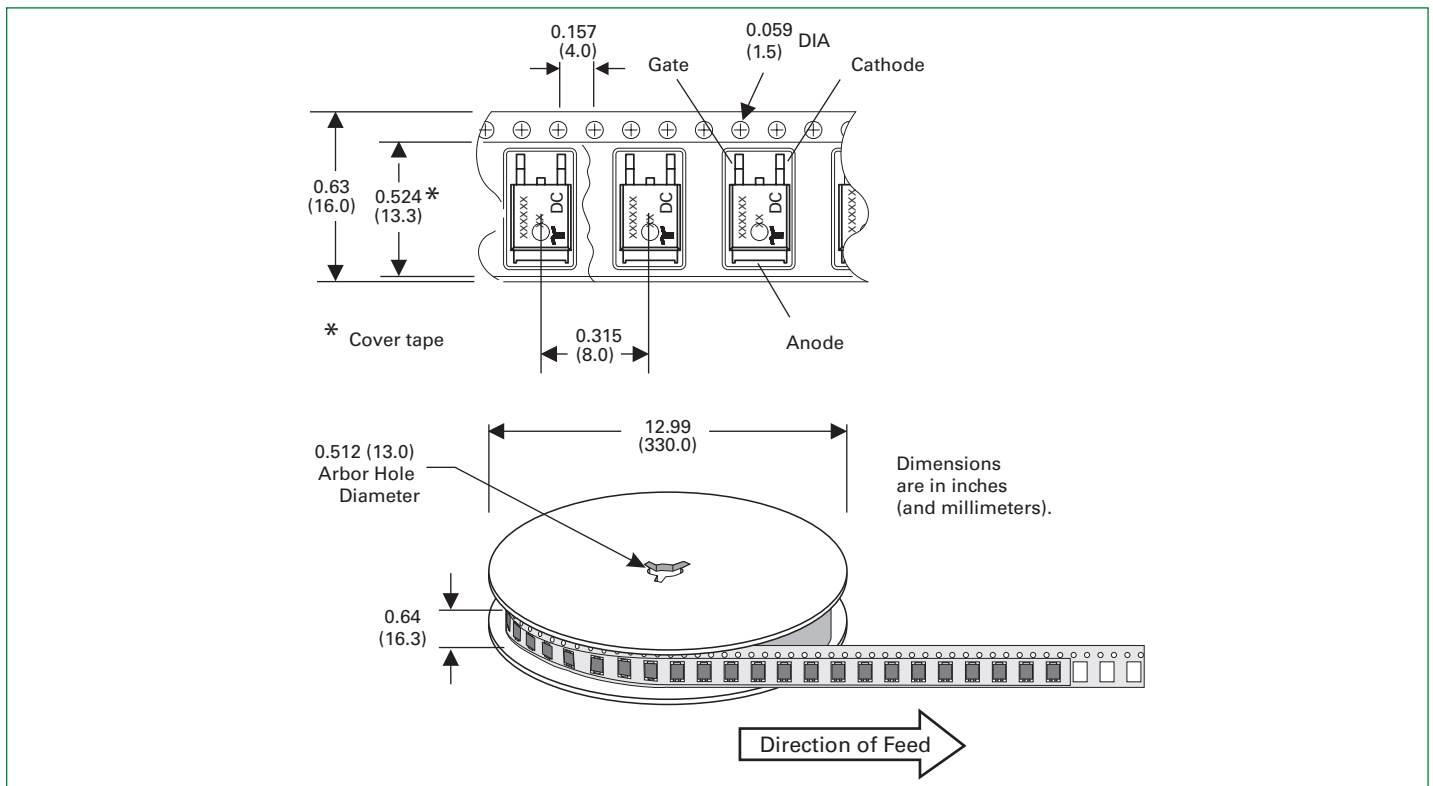
TO-252AA - (D Package)



**Date Code Marking**  
 Y: Year Code  
 M: Month Code  
 L: Location Code  
 DD: Serial Number

## TO-252 Embossed Carrier Reel Pack (RP) Specifications

Meets all EIA-418-2 Standards



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Part of:

